

### Description

The SX10N04SI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

$V_{DS} = 40V$   $I_D = 10A$

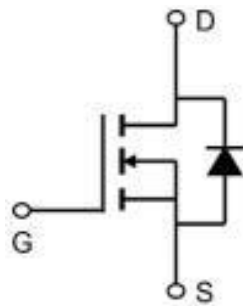
$R_{DS(ON)} < 22m\Omega @ V_{GS}=10V$

### Application

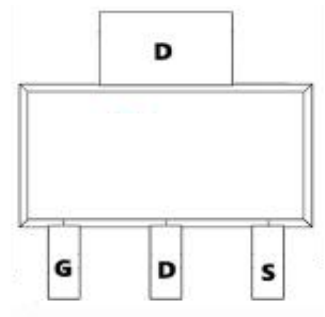
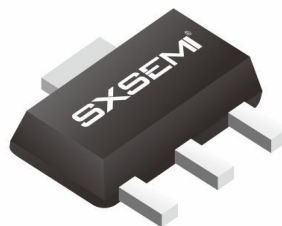
Automotive lighting

Load switch

Uninterruptible power supply



SOT-89-3L



### Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	40	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current <sup>1</sup>	10	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current <sup>1</sup>	6.7	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	50	A
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>3</sup>	31	mJ
I <sub>AS</sub>	Avalanche Current	25	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	1.9	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	125	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	15	°C/W

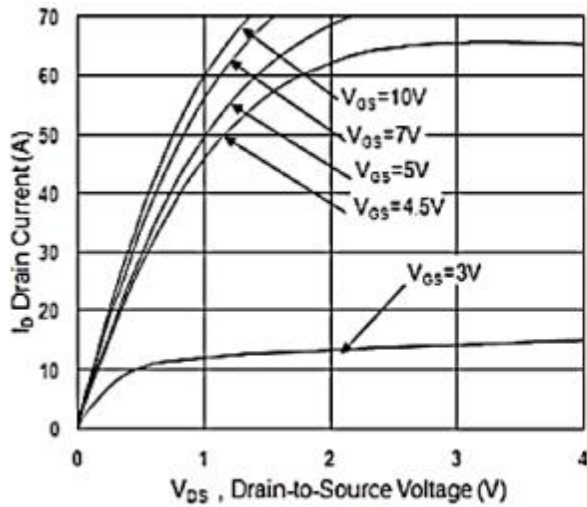
**Electrical Characteristics@T<sub>J</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	40	44	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA	---	0.032	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =7A	---	18	22	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =6A	---	23	30	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.4	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.8	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =32V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =32V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =7A	---	32	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz	---	2.1	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =32V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =7A	---	9.8	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.8	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.9	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =20V , V <sub>GS</sub> =10V , R <sub>G</sub> =3.3Ω I <sub>D</sub> =7A	---	2.8	---	ns
T <sub>r</sub>	Rise Time		---	40.4	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	22.8	---	
T <sub>f</sub>	Fall Time		---	6.4	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz	---	1013	---	pF
C <sub>oss</sub>	Output Capacitance		---	107	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	76	---	
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	8.4	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C	---	---	50	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>		---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =7A , dI/dt=100A/μs , T <sub>J</sub> =25°C	---	10	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	3.3	---	nC

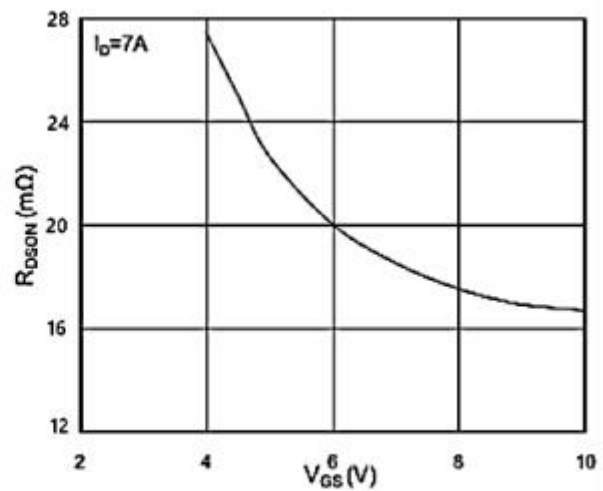
**Note :**

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

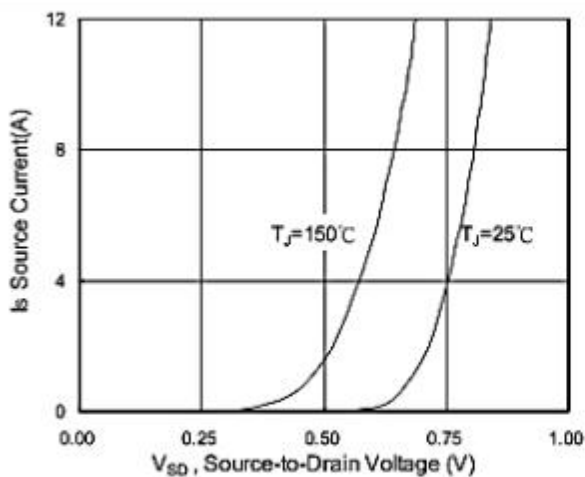
## Typical Characteristics



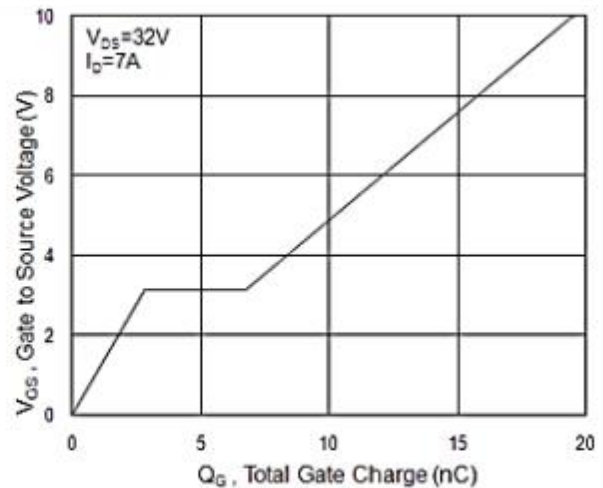
**Fig.1 Typical Output Characteristics**



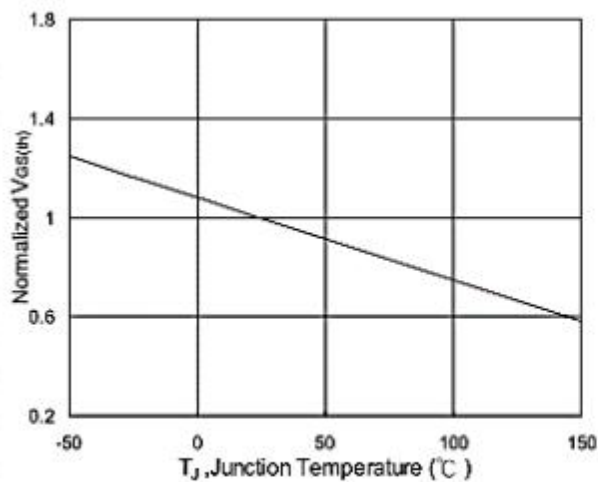
**Fig.2 On-Resistance vs. G-S Voltage**



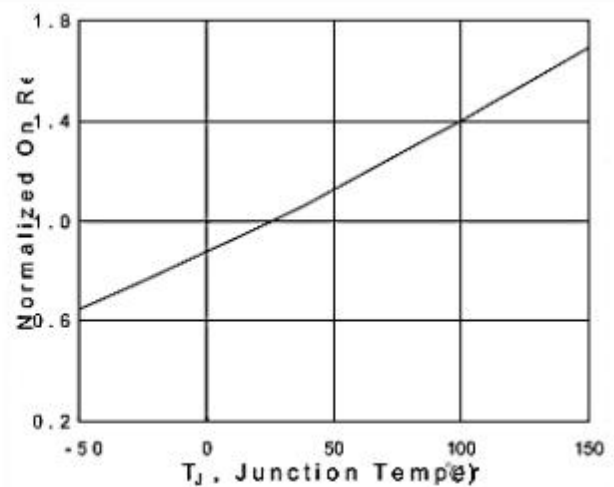
**Fig.3 Forward Characteristics of Reverse**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**

## Typical Characteristics

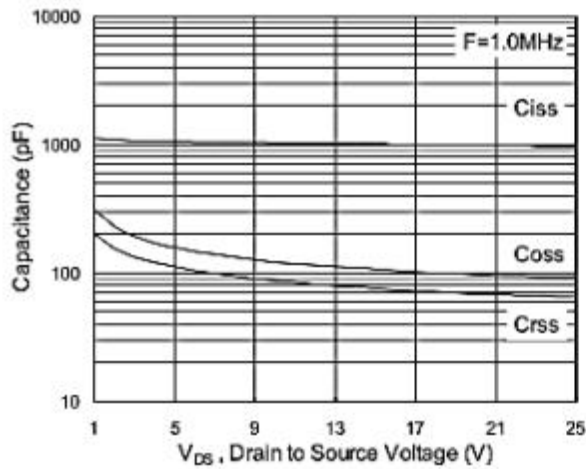


Fig.7 Capacitance

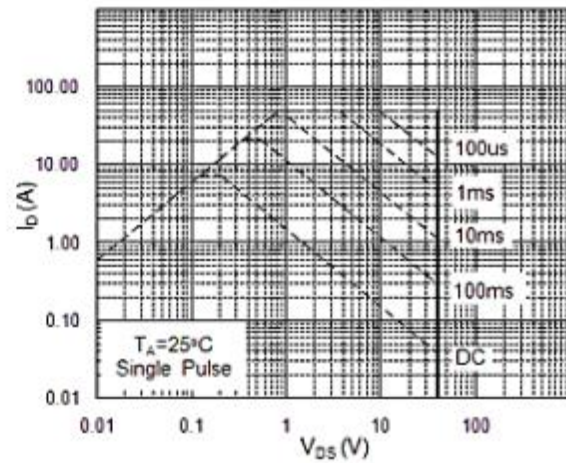


Fig.8 Safe Operating Area

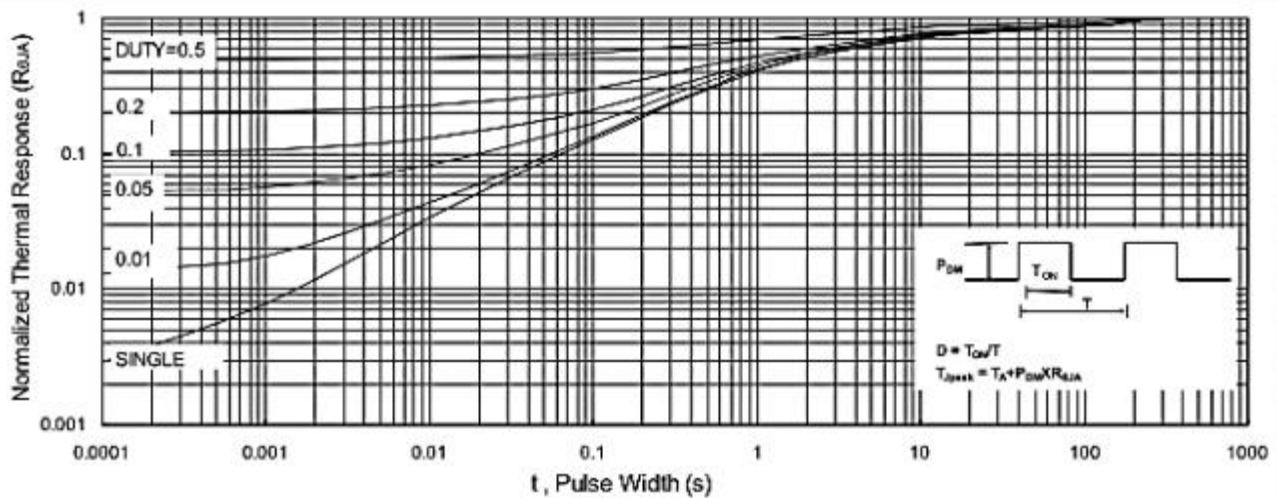


Fig.9 Normalized Maximum Transient Thermal Impedance

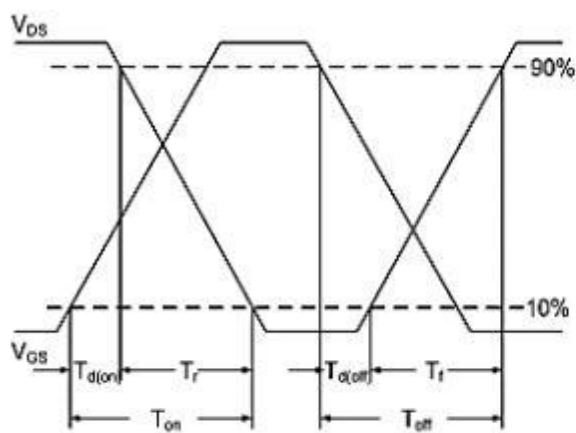


Fig.10 Switching Time Waveform

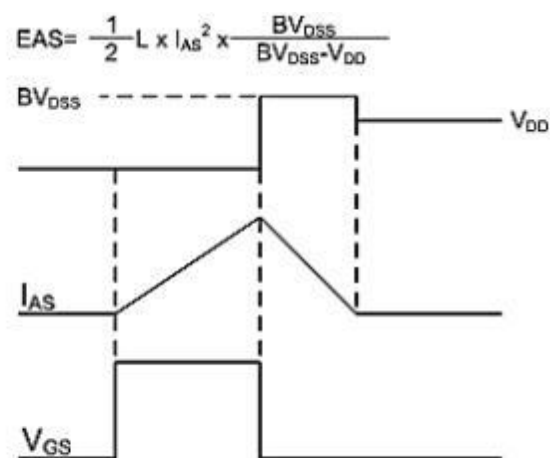
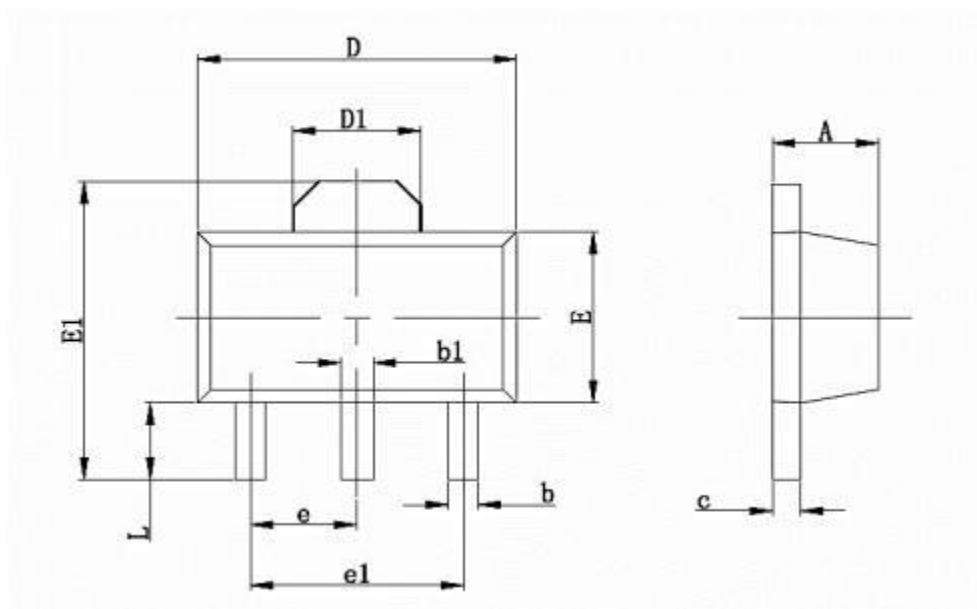


Fig.11 Unclamped Inductive Switching Waveform

## Package Mechanical Data:SOT89-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.350	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.350	2.550	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060TYP	
e1	3.000 TYP		0.118TYP	
L	0.900	1.100	0.035	0.047

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT89-3L		3000